

# MBT3946DW1T1G, SMBT3946DW1T1G

## Complementary General Purpose Transistor

The MBT3946DW1T1G device is a spin-off of our popular SOT-23/SOT-323 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-363-6 surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

### Features

- $h_{FE}$ , 100–300
- Low  $V_{CE(sat)}$ ,  $\leq 0.4$  V
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

**Table 1. MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage (NPN) (PNP)	$V_{CEO}$	40 –40	Vdc
Collector – Base Voltage (NPN) (PNP)	$V_{CBO}$	60 –40	Vdc
Emitter – Base Voltage (NPN) (PNP)	$V_{EBO}$	6.0 –5.0	Vdc
Collector Current – Continuous (NPN) (PNP)	$I_C$	200 –200	mAdc
Electrostatic Discharge	ESD	HBM Class 2 MM Class B	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

**Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Total Package Dissipation (Note 1) $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.

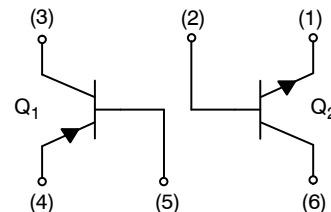


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<http://onsemi.com>

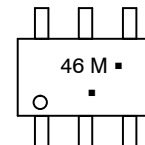


**SOT-363/SC-88  
CASE 419B  
STYLE 1**



**MBT3946DW1T1\***  
\*Q1 PNP  
Q2 NPN

### MARKING DIAGRAM



46 = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
MBT3946DW1T1G	SC-88 (Pb-Free)	3,000 / Tape & Reel
SMBT3946DW1T1G	SC-88 (Pb-Free)	3,000 / Tape & Reel
MBT3946DW1T2G	SC-88 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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**Table 3. ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage (Note 2) ( $I_C = 1.0\text{ mAdc}$ , $I_B = 0$ ) ( $I_C = -1.0\text{ mAdc}$ , $I_B = 0$ )	(NPN) (PNP)	$V_{(BR)CEO}$	40 –40	– –	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{Adc}$ , $I_E = 0$ ) ( $I_C = -10\text{ }\mu\text{Adc}$ , $I_E = 0$ )	(NPN) (PNP)	$V_{(BR)CBO}$	60 –40	– –	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{Adc}$ , $I_C = 0$ ) ( $I_E = -10\text{ }\mu\text{Adc}$ , $I_C = 0$ )	(NPN) (PNP)	$V_{(BR)EBO}$	6.0 –5.0	– –	Vdc
Base Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $V_{EB} = 3.0\text{ Vdc}$ ) ( $V_{CE} = -30\text{ Vdc}$ , $V_{EB} = -3.0\text{ Vdc}$ )	(NPN) (PNP)	$I_{BL}$	– –	50 –50	nAdc
Collector Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $V_{EB} = 3.0\text{ Vdc}$ ) ( $V_{CE} = -30\text{ Vdc}$ , $V_{EB} = -3.0\text{ Vdc}$ )	(NPN) (PNP)	$I_{CEX}$	– –	50 –50	nAdc
<b>ON CHARACTERISTICS</b> (Note 2)					
DC Current Gain ( $I_C = 0.1\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 100\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ )  ( $I_C = -0.1\text{ mAdc}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -1.0\text{ mAdc}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -10\text{ mAdc}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -50\text{ mAdc}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -100\text{ mAdc}$ , $V_{CE} = -1.0\text{ Vdc}$ )	(NPN)       (PNP)	$h_{FE}$	40 70 100 60 30  60 80 100 60 30	– – 300 – –  – – 300 – –	–
Collector–Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ ) ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )  ( $I_C = -10\text{ mAdc}$ , $I_B = -1.0\text{ mAdc}$ ) ( $I_C = -50\text{ mAdc}$ , $I_B = -5.0\text{ mAdc}$ )	(NPN)   (PNP)	$V_{CE(sat)}$	– –  – –	0.2 0.3  –0.25 –0.4	Vdc
Base–Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ ) ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )  ( $I_C = -10\text{ mAdc}$ , $I_B = -1.0\text{ mAdc}$ ) ( $I_C = -50\text{ mAdc}$ , $I_B = -5.0\text{ mAdc}$ )	(NPN)   (PNP)	$V_{BE(sat)}$	0.65 –  –0.65 –	0.85 0.95  –0.85 –0.95	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>					
Current–Gain – Bandwidth Product ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ ) ( $I_C = -10\text{ mAdc}$ , $V_{CE} = -20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	(NPN) (PNP)	$f_T$	300 250	– –	MHz
Output Capacitance ( $V_{CB} = 5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ ) ( $V_{CB} = -5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	(NPN) (PNP)	$C_{obo}$	– –	4.0 4.5	pF
Input Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ ) ( $V_{EB} = -0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	(NPN) (PNP)	$C_{ibo}$	– –	8.0 10.0	pF
Input Impedance ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ ) ( $V_{CE} = -10\text{ Vdc}$ , $I_C = -1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	(NPN) (PNP)	$h_{ie}$	1.0 2.0	10 12	k $\Omega$
Voltage Feedback Ratio ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ ) ( $V_{CE} = -10\text{ Vdc}$ , $I_C = -1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	(NPN) (PNP)	$h_{re}$	0.5 0.1	8.0 10	$\times 10^{-4}$
Small–Signal Current Gain ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ ) ( $V_{CE} = -10\text{ Vdc}$ , $I_C = -1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	(NPN) (PNP)	$h_{fe}$	100 100	400 400	–

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**Table 4. ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (continued)

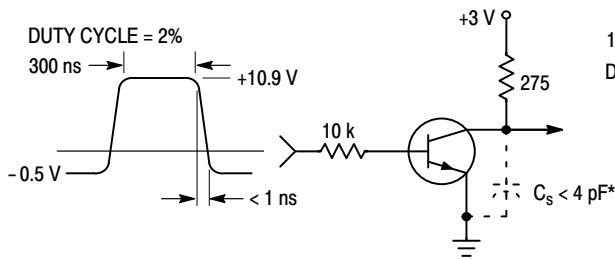
Characteristic	Symbol	Min	Max	Unit
Output Admittance ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ ) ( $V_{CE} = -10\text{ Vdc}$ , $I_C = -1.0\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$ (NPN) (PNP)	1.0 3.0	40 60	$\mu\text{mhos}$
Noise Figure ( $V_{CE} = 5.0\text{ Vdc}$ , $I_C = 100\ \mu\text{A}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ ) ( $V_{CE} = -5.0\text{ Vdc}$ , $I_C = -100\ \mu\text{A}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	NF (NPN) (PNP)	- -	5.0 4.0	dB

## SWITCHING CHARACTERISTICS

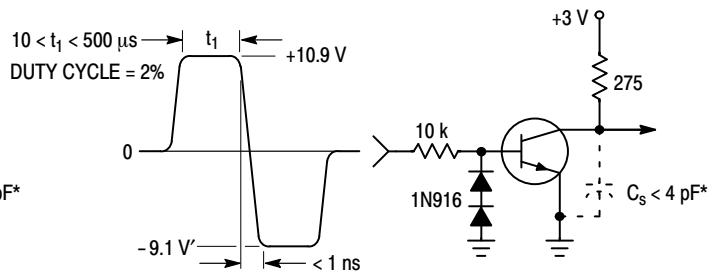
Delay Time ( $V_{CC} = 3.0\text{ Vdc}$ , $V_{BE} = -0.5\text{ Vdc}$ ) ( $V_{CC} = -3.0\text{ Vdc}$ , $V_{BE} = 0.5\text{ Vdc}$ )	(NPN) (PNP)	$t_d$	- -	35 35	ns
Rise Time ( $I_C = 10\text{ mAdc}$ , $I_{B1} = 1.0\text{ mAdc}$ ) ( $I_C = -10\text{ mAdc}$ , $I_{B1} = -1.0\text{ mAdc}$ )	(NPN) (PNP)	$t_r$	- -	35 35	
Storage Time ( $V_{CC} = 3.0\text{ Vdc}$ , $I_C = 10\text{ mAdc}$ ) ( $V_{CC} = -3.0\text{ Vdc}$ , $I_C = -10\text{ mAdc}$ )	(NPN) (PNP)	$t_s$	- -	200 225	ns
Fall Time ( $I_{B1} = I_{B2} = 1.0\text{ mAdc}$ ) ( $I_{B1} = I_{B2} = -1.0\text{ mAdc}$ )	(NPN) (PNP)	$t_f$	- -	50 75	

2. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ ; Duty Cycle  $\leq 2.0\%$ .

### (NPN)



**Figure 1. Delay and Rise Time Equivalent Test Circuit**

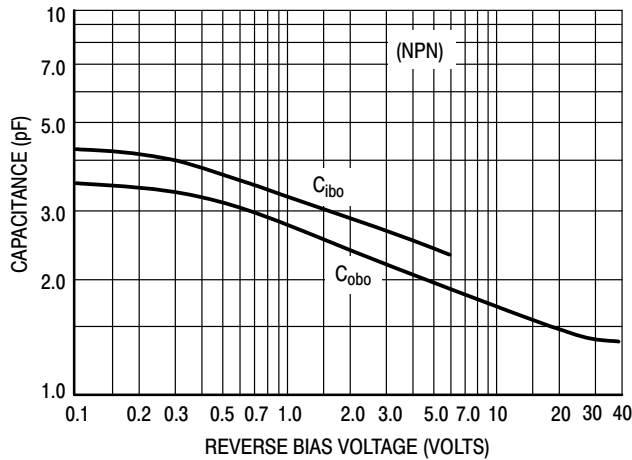


**Figure 2. Storage and Fall Time Equivalent Test Circuit**

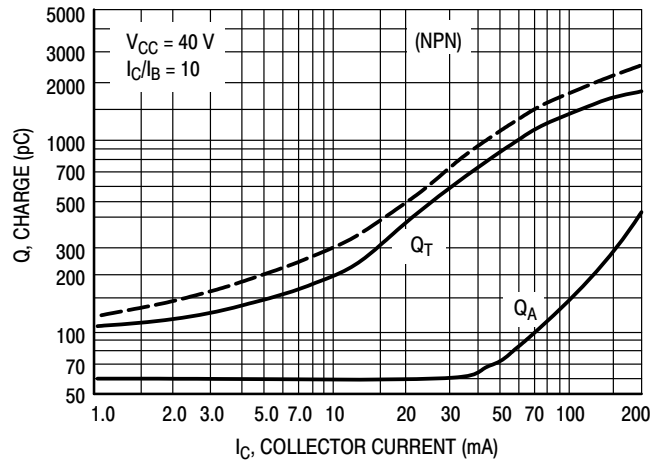
\* Total shunt capacitance of test jig and connectors

## TYPICAL TRANSIENT CHARACTERISTICS

—  $T_J = 25^\circ\text{C}$   
- -  $T_J = 125^\circ\text{C}$



**Figure 3. Capacitance**



**Figure 4. Charge Data**

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(NPN)

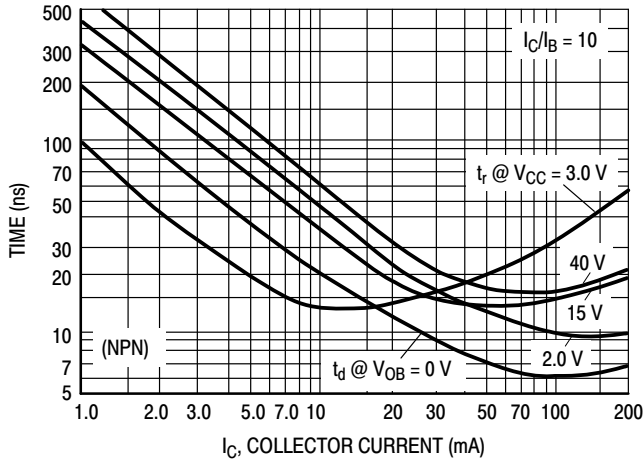


Figure 5. Turn-On Time

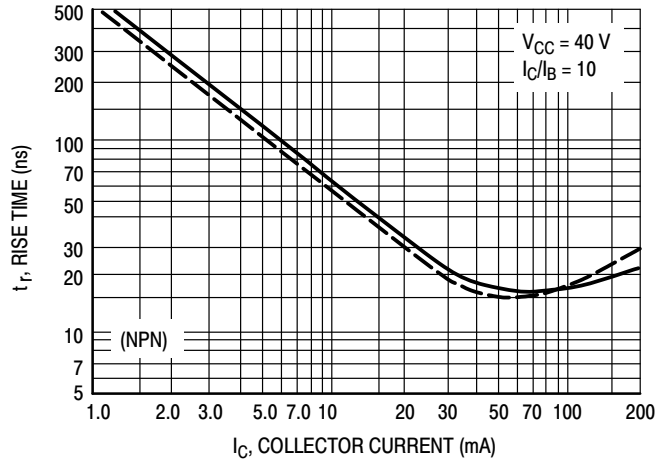


Figure 6. Rise Time

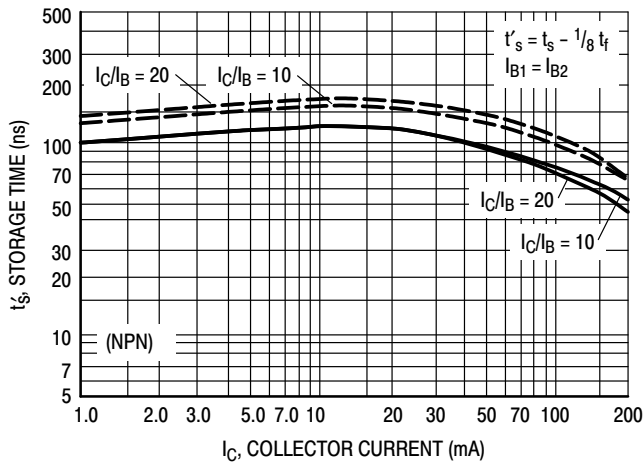


Figure 7. Storage Time

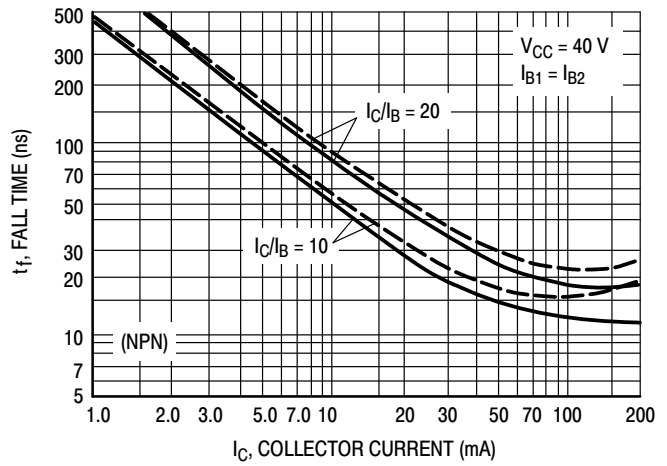


Figure 8. Fall Time

## TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

( $V_{CE} = 5.0$  Vdc,  $T_A = 25^\circ\text{C}$ , Bandwidth = 1.0 Hz)

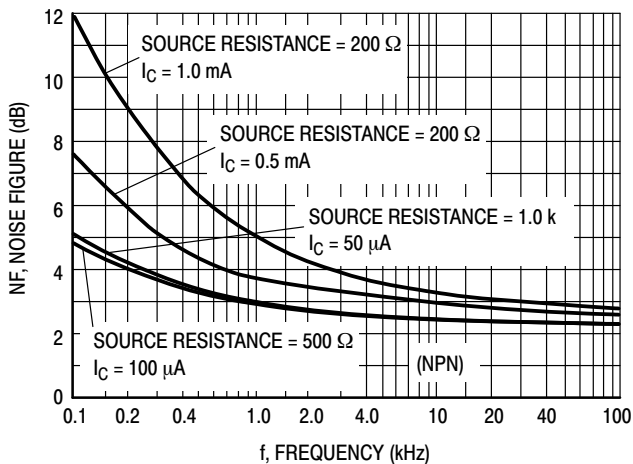


Figure 9. Noise Figure

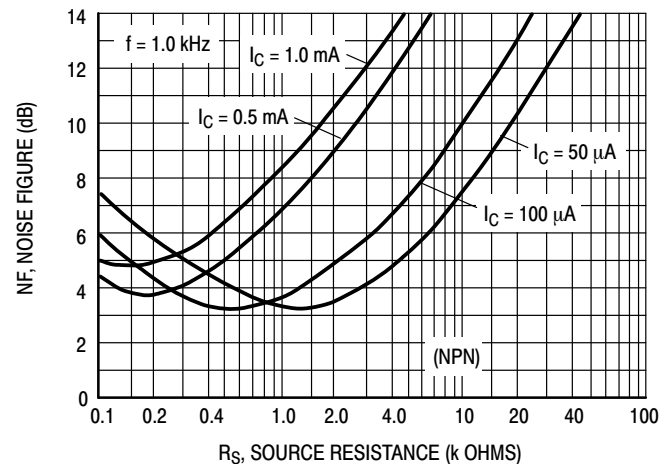


Figure 10. Noise Figure

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## (NPN) h PARAMETERS

( $V_{CE} = 10 \text{ Vdc}$ ,  $f = 1.0 \text{ kHz}$ ,  $T_A = 25^\circ\text{C}$ )

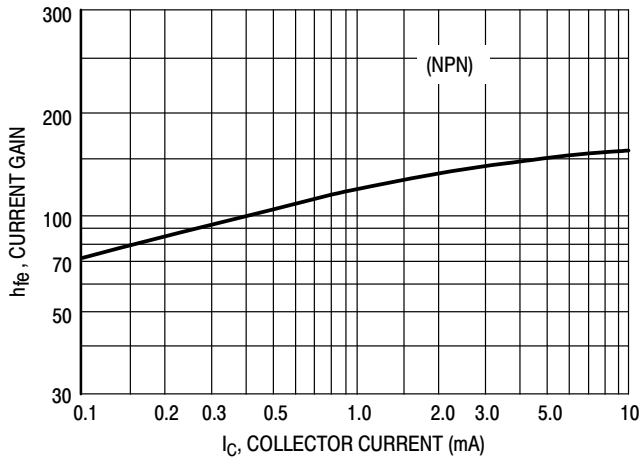


Figure 11. Current Gain

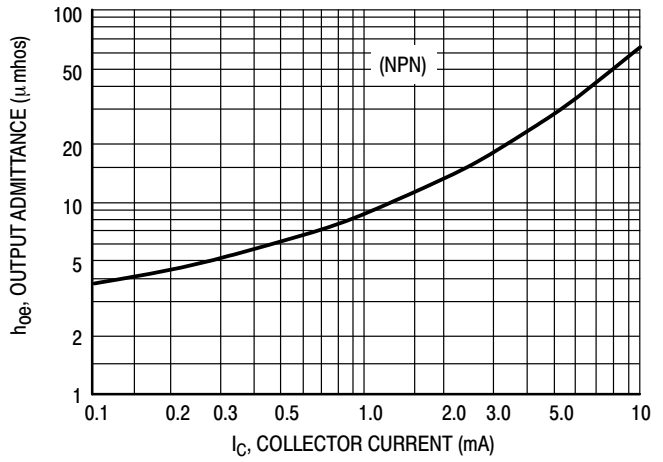


Figure 12. Output Admittance

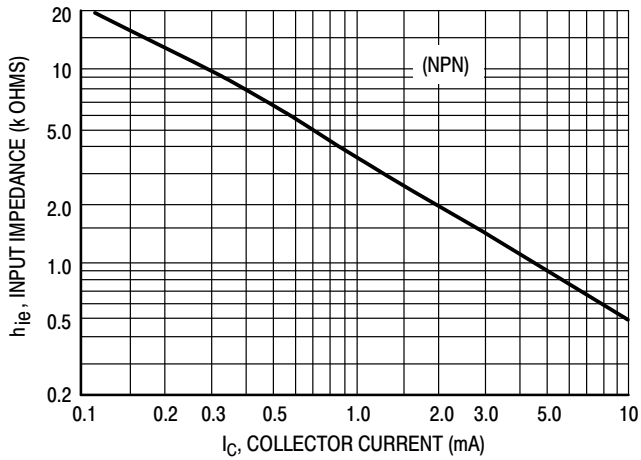


Figure 13. Input Impedance

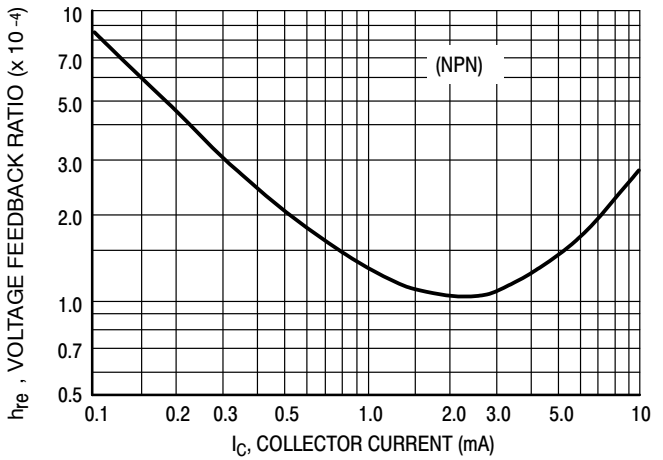


Figure 14. Voltage Feedback Ratio

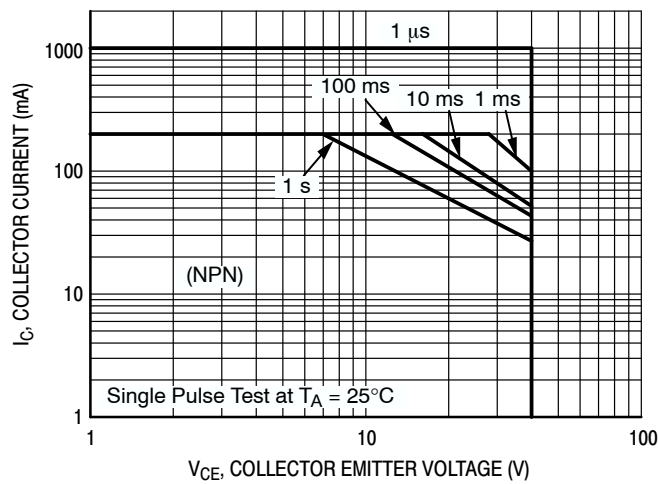


Figure 15. Safe Operating Area

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## (NPN) TYPICAL STATIC CHARACTERISTICS



Figure 16. DC Current Gain

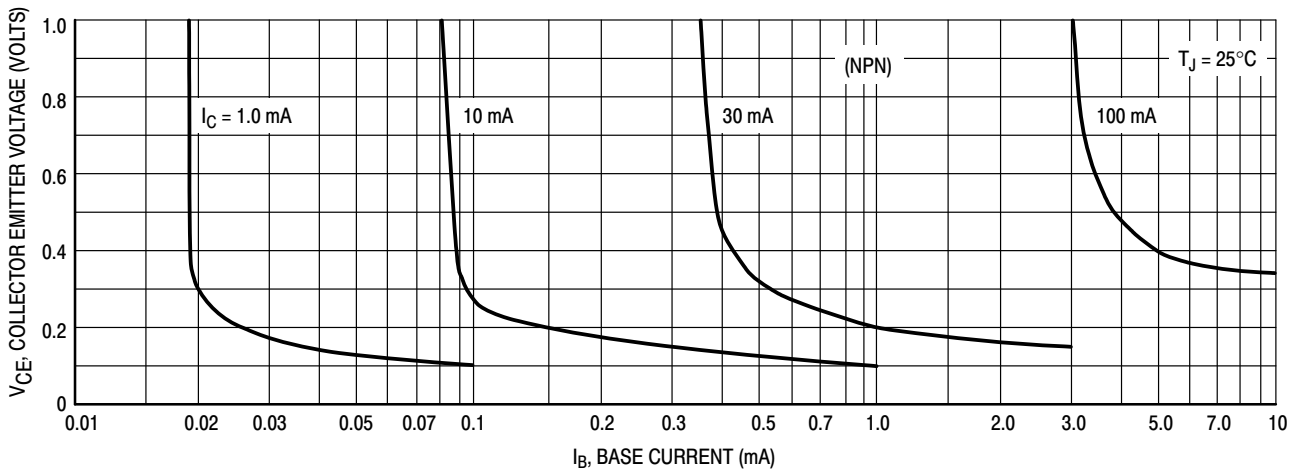


Figure 17. Collector Saturation Region

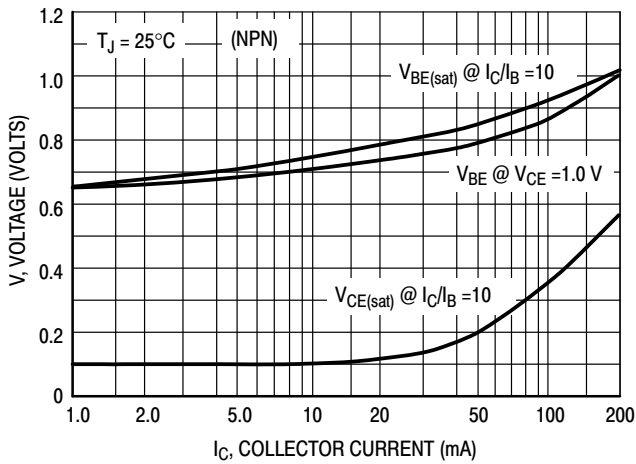


Figure 18. "ON" Voltages

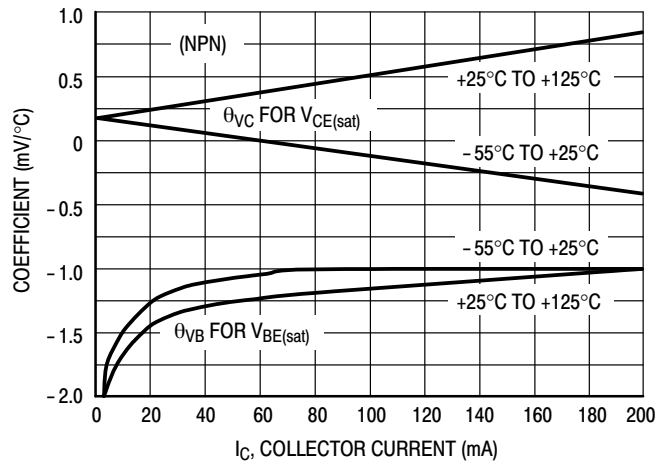


Figure 19. Temperature Coefficients

# MBT3946DW1T1G, SMBT3946DW1T1G

(PNP)

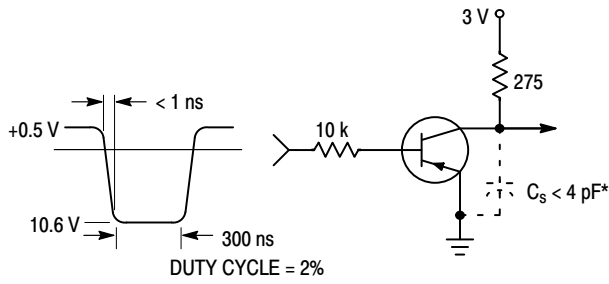


Figure 20. Delay and Rise Time Equivalent Test Circuit

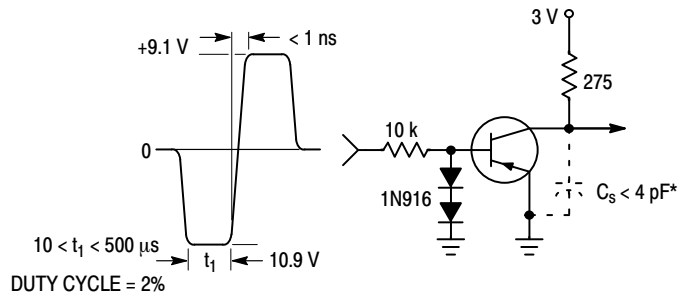


Figure 21. Storage and Fall Time Equivalent Test Circuit

\* Total shunt capacitance of test jig and connectors

## TYPICAL TRANSIENT CHARACTERISTICS

—  $T_J = 25^\circ\text{C}$   
 - - -  $T_J = 125^\circ\text{C}$

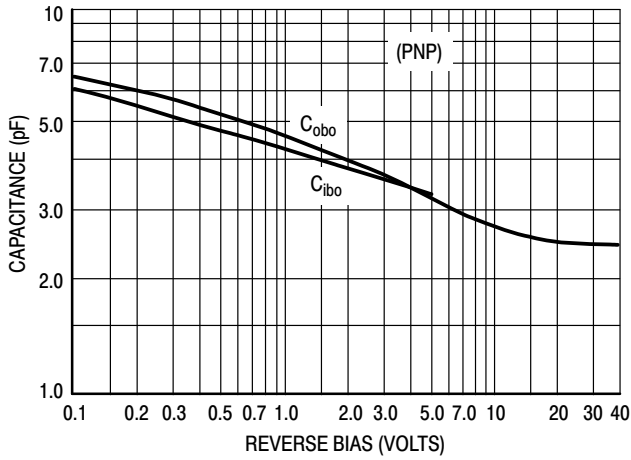


Figure 22. Capacitance

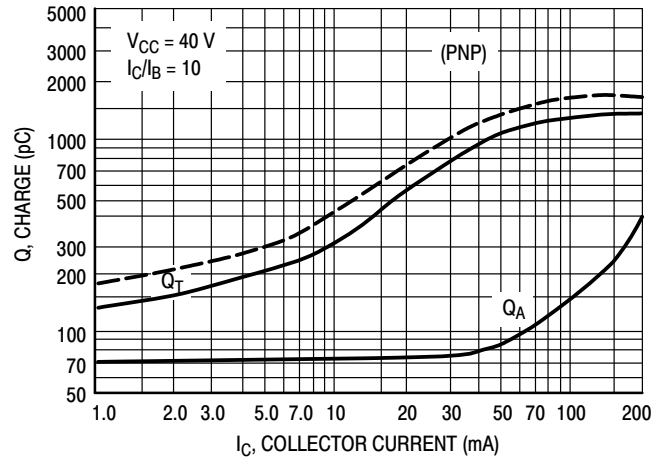


Figure 23. Charge Data

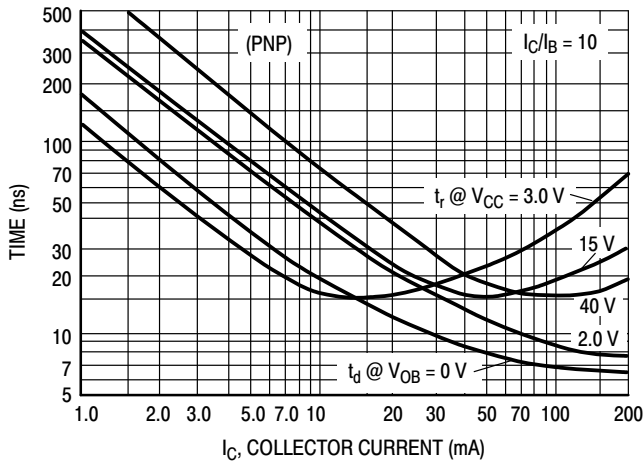


Figure 24. Turn-On Time

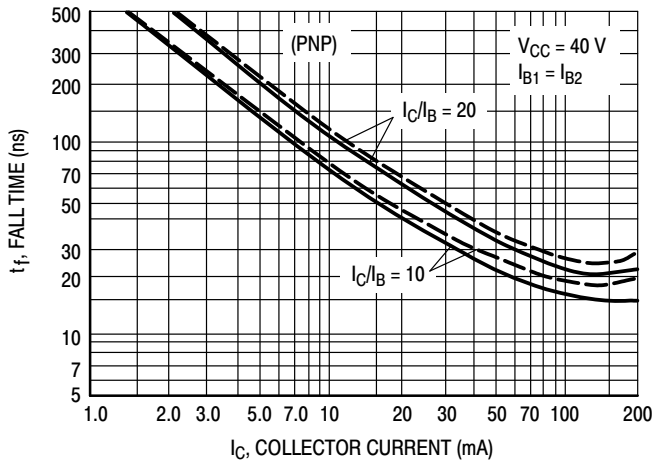


Figure 25. Fall Time

# MBT3946DW1T1G, SMBT3946DW1T1G

(PNP)

## TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

( $V_{CE} = -5.0$  Vdc,  $T_A = 25^\circ\text{C}$ , Bandwidth = 1.0 Hz)



Figure 26.

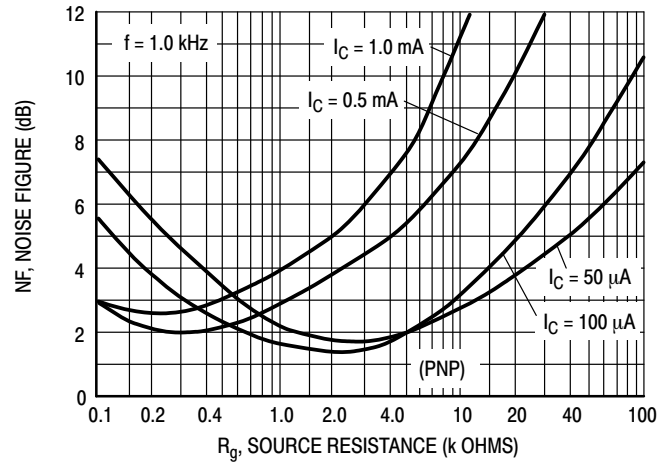


Figure 27.

## h PARAMETERS

( $V_{CE} = -10$  Vdc,  $f = 1.0$  kHz,  $T_A = 25^\circ\text{C}$ )

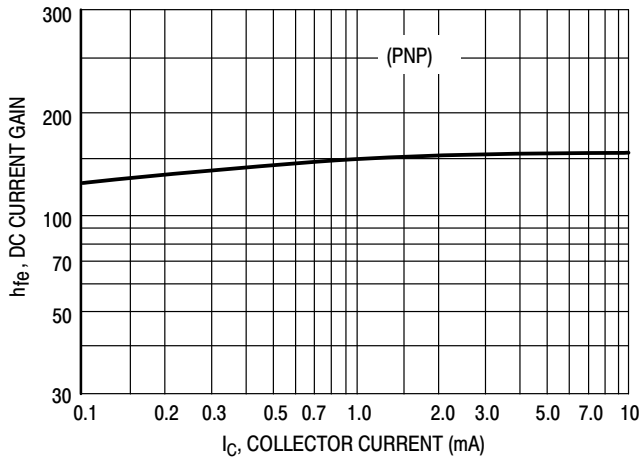


Figure 28. Current Gain

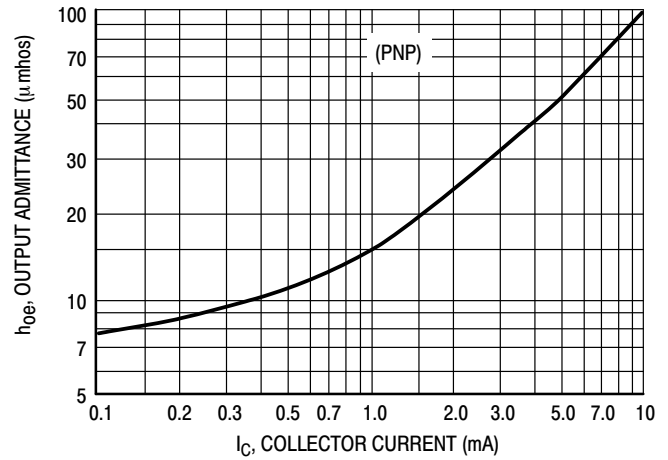


Figure 29. Output Admittance

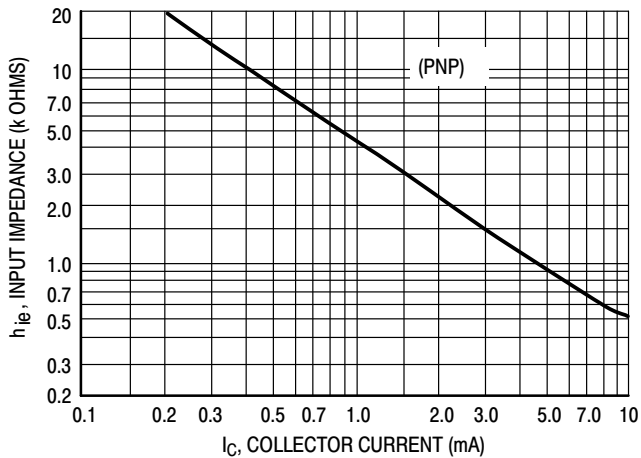


Figure 30. Input Impedance

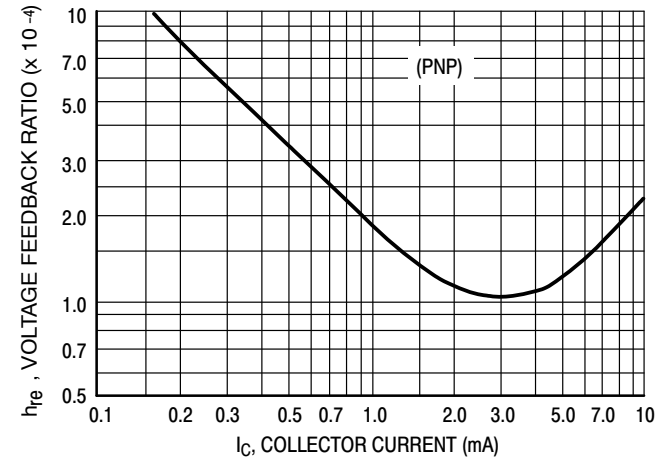


Figure 31. Voltage Feedback Ratio



# MBT3946DW1T1G, SMT3946DW1T1G

(PNP)

## TYPICAL STATIC CHARACTERISTICS

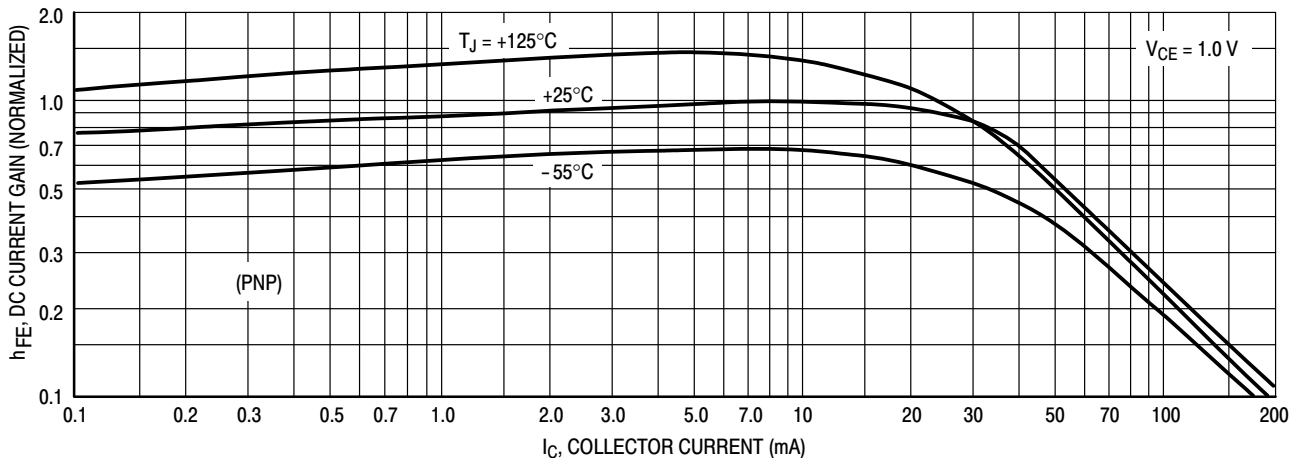


Figure 32. DC Current Gain

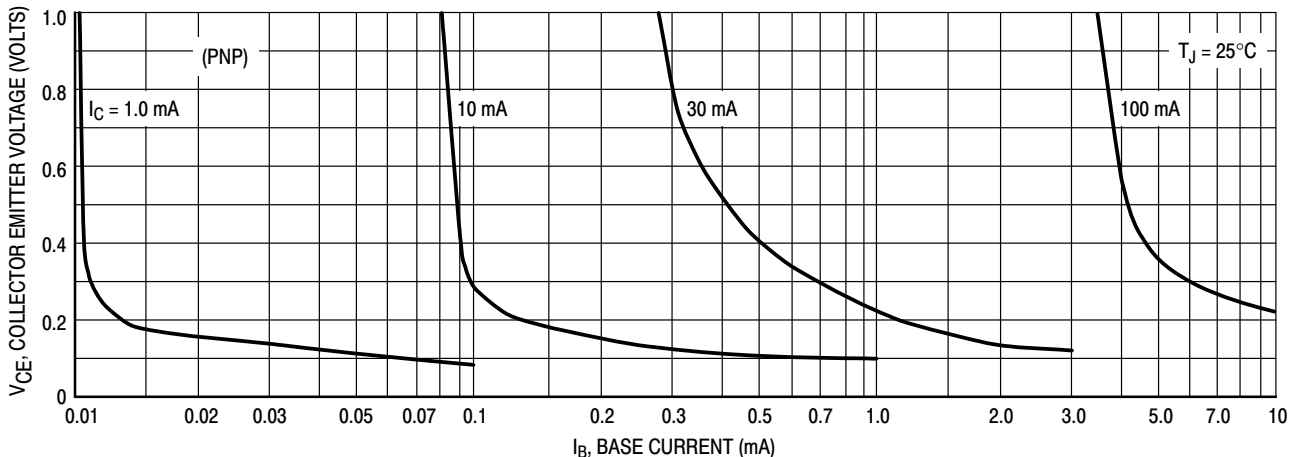


Figure 33. Collector Saturation Region

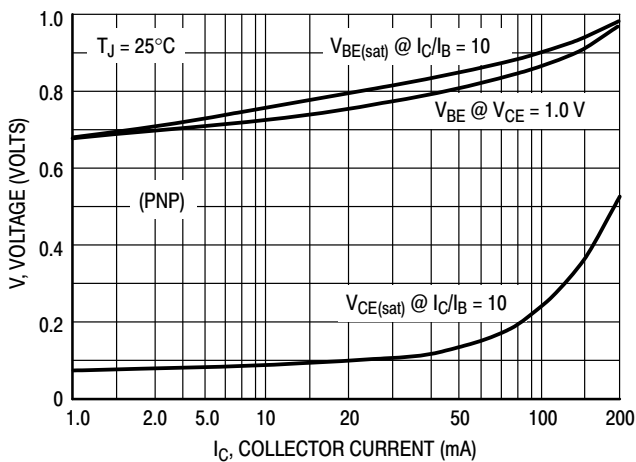


Figure 34. "ON" Voltages

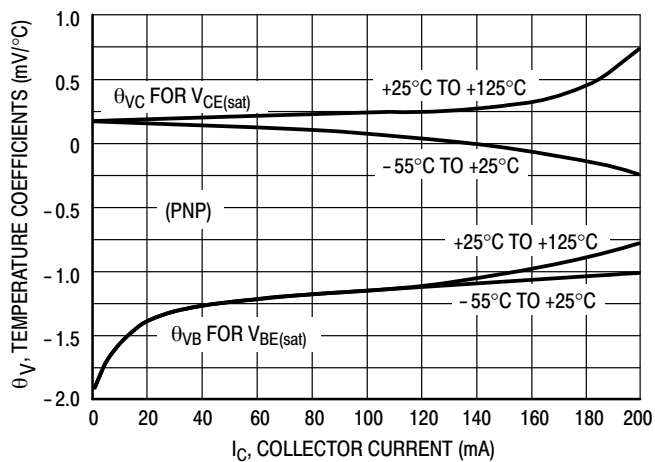


Figure 35. Temperature Coefficients

# MBT3946DW1T1G, SMBT3946DW1T1G

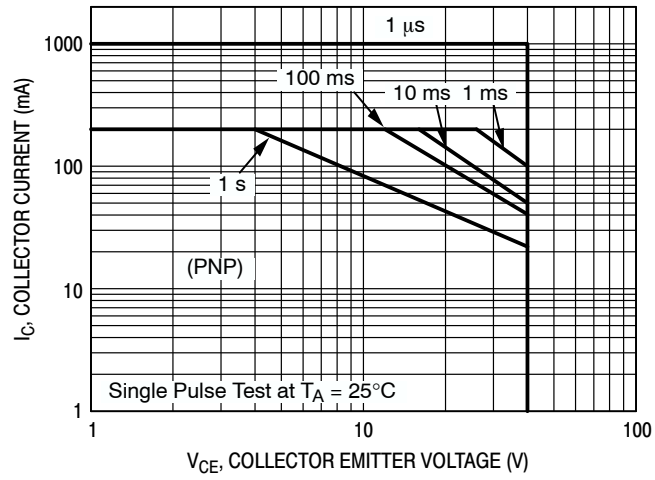


Figure 36. Safe Operating Area

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

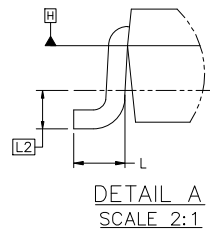
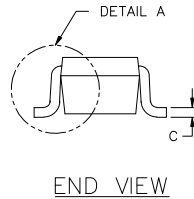
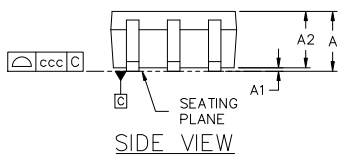
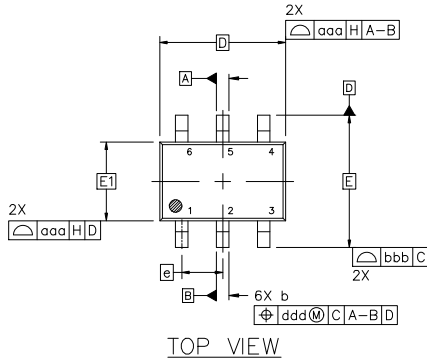


**SC-88 2.00x1.25x0.90, 0.65P**  
CASE 419B-02  
ISSUE Z

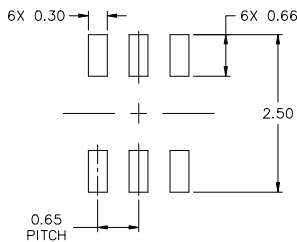
DATE 18 APR 2024

NOTES:

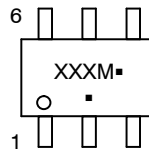
1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code\*
- = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**STYLES ON PAGE 2**

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<b>DESCRIPTION:</b>	<b>SC-88 2.00x1.25x0.90, 0.65P</b>	<b>PAGE 1 OF 2</b>

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**SC-88 2.00x1.25x0.90, 0.65P**  
**CASE 419B-02**  
**ISSUE Z**

DATE 18 APR 2024

<b>STYLE 1:</b> PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	<b>STYLE 2:</b> CANCELLED	<b>STYLE 3:</b> CANCELLED	<b>STYLE 4:</b> PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	<b>STYLE 5:</b> PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	<b>STYLE 6:</b> PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
<b>STYLE 7:</b> PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	<b>STYLE 8:</b> CANCELLED	<b>STYLE 9:</b> PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	<b>STYLE 10:</b> PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	<b>STYLE 11:</b> PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	<b>STYLE 12:</b> PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
<b>STYLE 13:</b> PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	<b>STYLE 14:</b> PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	<b>STYLE 15:</b> PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	<b>STYLE 16:</b> PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	<b>STYLE 17:</b> PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	<b>STYLE 18:</b> PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
<b>STYLE 19:</b> PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	<b>STYLE 20:</b> PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	<b>STYLE 21:</b> PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	<b>STYLE 22:</b> PIN 1. D1 (i) 2. GND 3. D2 (j) 4. D2 (c) 5. VBUS 6. D1 (c)	<b>STYLE 23:</b> PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	<b>STYLE 24:</b> PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
<b>STYLE 25:</b> PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	<b>STYLE 26:</b> PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	<b>STYLE 27:</b> PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	<b>STYLE 28:</b> PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	<b>STYLE 29:</b> PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	<b>STYLE 30:</b> PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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